	Substitute for	form 1449/PTO			Application Number	10/788,857		
0	INE				Filing Date:	February 26, 2004		
/	\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \	Information	Disclosure)	First Named Inventor:	Chao I. WU 2824		
_ FEB	0 7 2006 📽)	Statement B	By Applican	t	Art Unit:			
PATER	/بير	(Use as many she	ets as necessary)		Examiner Name:	N. Nguyen		
13	£ /				Attorney Docket Number:	MXICP031		
N/A	DEMEDICAL	11	of	1				

U.S. Patent Documents

U.S. Patent Documents									
Examiner Initial	Cite No.	Document No.	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, where Relevant Passages or Relevant Figures Appear				
NW	Α	6,011,725	1/2000	Eitan					
NN	В	6,487,114	11/2002	Jong et al.					
	С								
	D								
	E								
	F								
	G								
	Н								
	J								
	K								

Foreign Patent Documents

Examiner Initial	Cite No.	Foreign Patent Document No.	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, where Relevant Passages or Relevant Figures Appear	Translation YES NO		
<u> </u>			<u> </u>		Appear	 	T	
	М					 		
	N							
	0							
	Р							
	Q							

Non Patent Literature Documents

		THE TAX TO
Examiner Initial	Cite No.	Include name of author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
MM	R	T. Y. CHAN et al., "A True Single-Transistor Oxide-Nitride-Oxide EEPROM Device," IEEE Electron Device Letters, Vol. EDL-8, No. 3, March 1987, pp. 93-95
	S	
	T	
	U	
	V	
	W	

	 Δ						i		•
Examiner Signature	Van	N	\ <u>\</u>	m	Date Considered	2	24	اه	<u> </u>
	 				 		,		

Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.